

200mm monitor wafer specification

No.	Characteristics	Specification value	Unit	Remark
1	Growth Method	CZ	-	
2	Conductive Type (dopant)	P (Boron)	-	
3	Resistivity	1-100	ohm cm	
4	RRV-max	-	%	
5	Crystal Orientation & Angle	<100>+/-1°		
6	Lifetime	-	μs	
7	Oxygen Concentration	-	atoms/cm ³	
8	Carbon Concentration	-	atoms/cm ³	
9	Etch Pit density (EPD)	-	er/cm ³	
10	Notch/OF	Notch		
11	Notch Location & Angle	(110)+/-1°		
12	Notch Shape & Angle	-	degree	SEMI
13	Notch Depth	1mm+0.25mm-0.00	mm	SEMI
14	Diameter	200+/-0.2	mm	
15	Total thickness	725+/-25	μm	
16	Edge Shape & Angle	Machine Chamfer(22°)		
17	Front Surface Condition	Polished	-	
18	Back Surface Condition	Etched	-	
19	TTV	10	μm	
20	GBIR		μm	
21	Warp/ Bow	≤40	μm	
22	Particle	0.2 ≤30	μm/er	
23	Lazer Mark (Back surface)	None		
24	Crack / Chip	None	mm	
25	Scratch	None		
26	Pin Hole	None		
27	Back Surface Scratch	L≤D/2	mm	
28	Lazer marking (Surface)	None		
29	Lazer marking (Backside)	None		
30	Product case transration	cassette	-	
31	Packing method translation	Al pack	-	
32	Surface Metals	≤1E10	atoms/cm ²	Al, Na, Fe, Cr, Cu
	(Line Security translation)			Ni, Zn, Ca, K, Mg